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[10191/1629]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Franz LAERMER et al.
Serial No. : To Be Assigned
Filed : Herewith
For : METHOD OF PLASMA
ETCHING OF SILICON

Art Unit : To Be Assigned
Examiner : To Be Assigned

Assistant Commissioner
for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

SIR:

Please amend the above-identified application before examination, as set forth below.

IN THE SPECIFICATION:

Page 1, before line 1, insert:

--FIELD OF THE INVENTION--.

Page 1, delete lines 3 to 6, and insert --silicon--.

Page 1, before line 8, insert:

--BACKGROUND INFORMATION--.

Page 1, delete line 8, and insert --In German Published Patent Application No. 197 06 682
is discussed a method of--.

Page 1, line 17, change "proposed" to --discussed--.

EL 302 702 614